



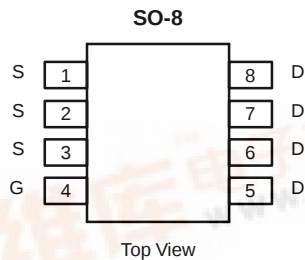
Si4896DY
Vishay Siliconix

N-Channel 80-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
80	0.0165 @ $V_{GS} = 10$ V	9.5
	0.022 @ $V_{GS} = 6.0$ V	8.3

TrenchFET®
Power MOSFETs



Ordering Information: Si4896DY
Si4896DY-T1 (with Tape and Reel)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	80		V
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	9.5	6.7	A
	T _A = 70°C		7.6	5.4	
Pulsed Drain Current		I _{DM}	50		
Avalanch Current	L = 0.1 mH	I _{AS}	40		
Continuous Source Current (Diode Conduction) ^a		I _S	2.8	1.4	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	3.1	1.56	W
	T _A = 70°C		2.0	1.0	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	33	40	$^\circ\text{C/W}$
	Steady State		65	80	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	17	21	

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

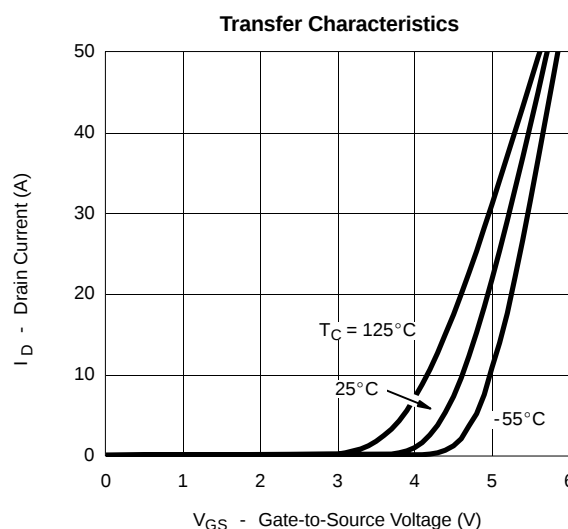
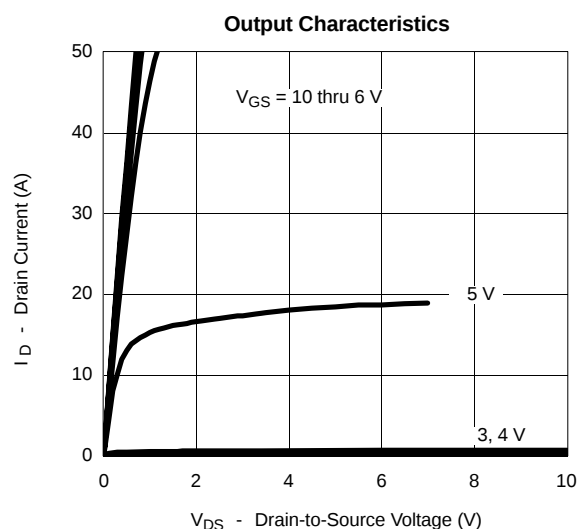
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2.0			V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 64\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 64\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	50			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$		0.0135	0.0165	Ω
		$V_{GS} = 6.0\ \text{V}$, $I_D = 8.0\ \text{A}$		0.0175	0.022	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 10\ \text{A}$		25		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.8\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.75	1.1	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 40\ \text{V}$, $V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$		34	41	nC
Gate-Source Charge	Q_{gs}			7.5		
Gate-Drain Charge	Q_{gd}			11.0		
Gate Resistance	R_g		0.2	0.85	1.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 40\ \text{V}$, $R_L = 40\ \Omega$ $I_D \approx 1.0\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		17	25	ns
Rise Time	t_r			11	17	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	t_f			31	45	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.8\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		45	75	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

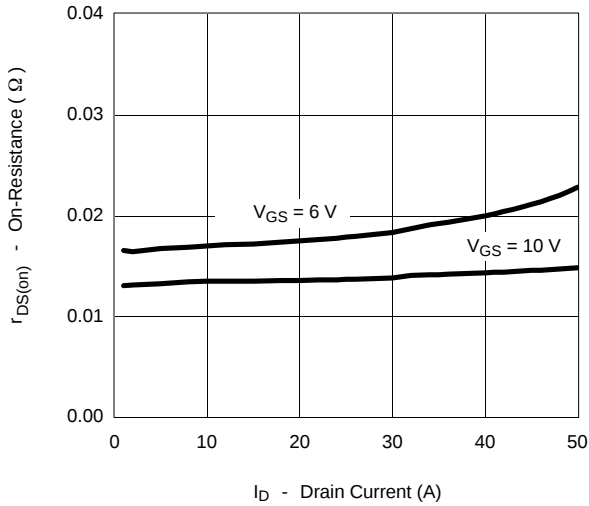
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



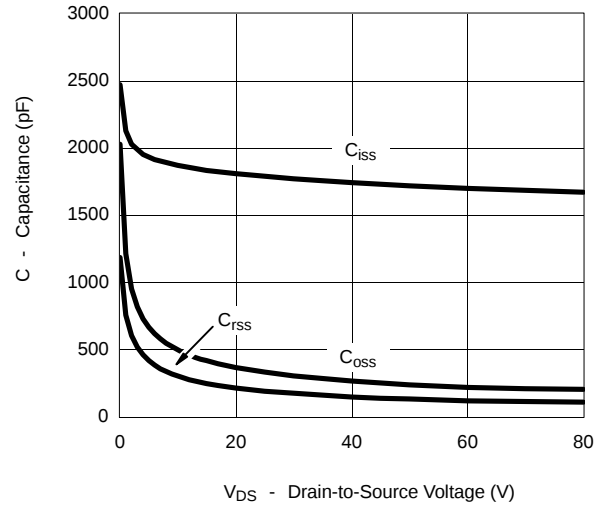


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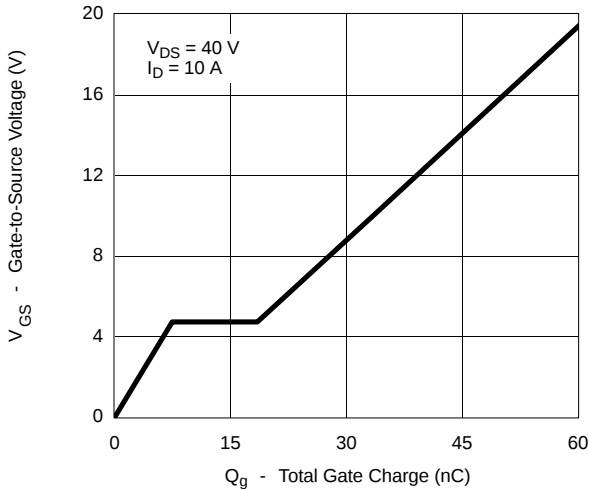
On-Resistance vs. Drain Current



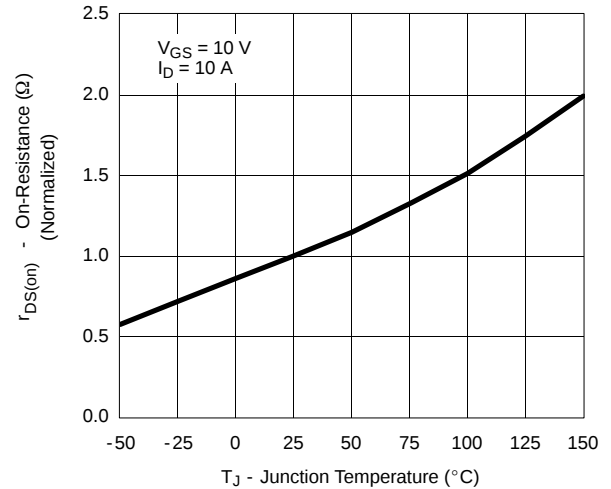
Capacitance



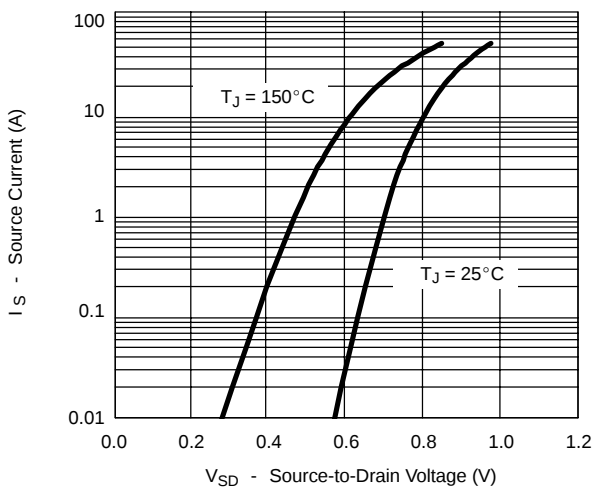
Gate Charge



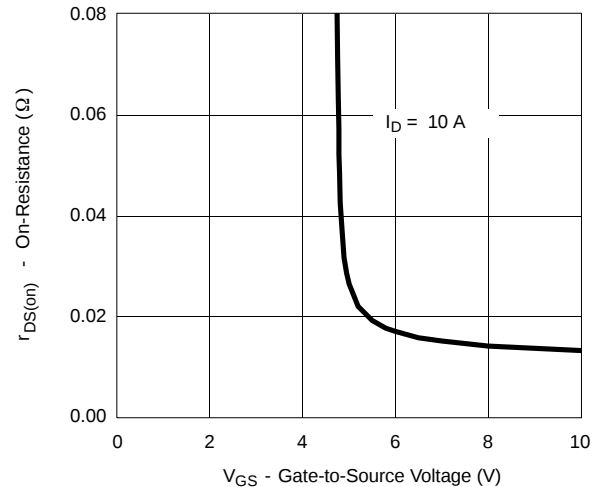
On-Resistance vs. Junction Temperature



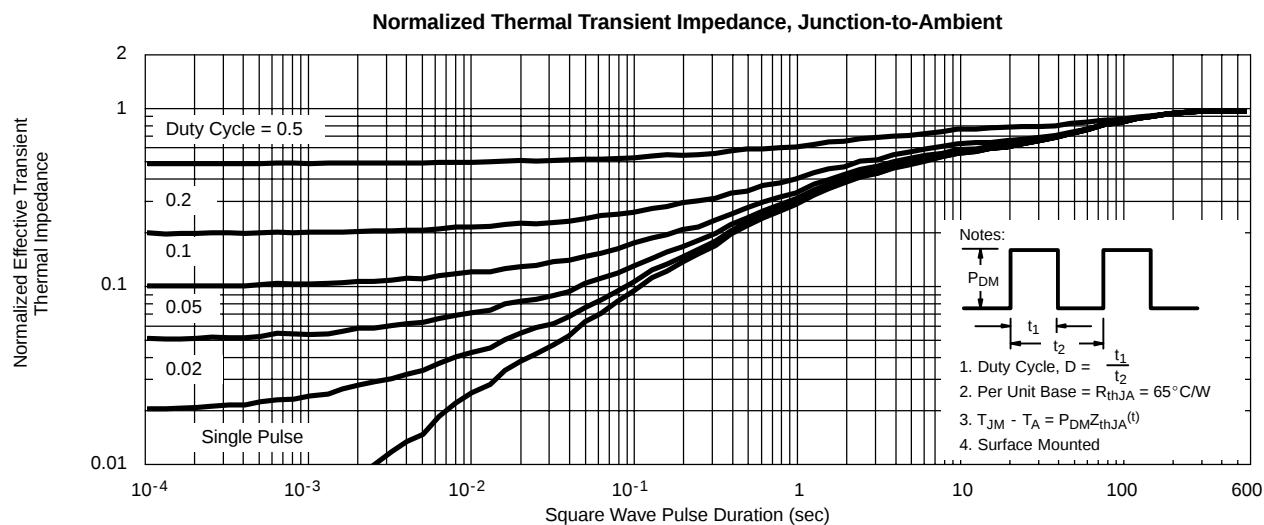
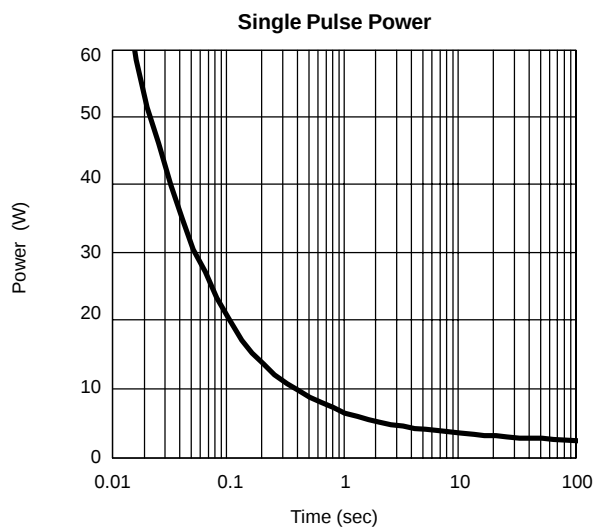
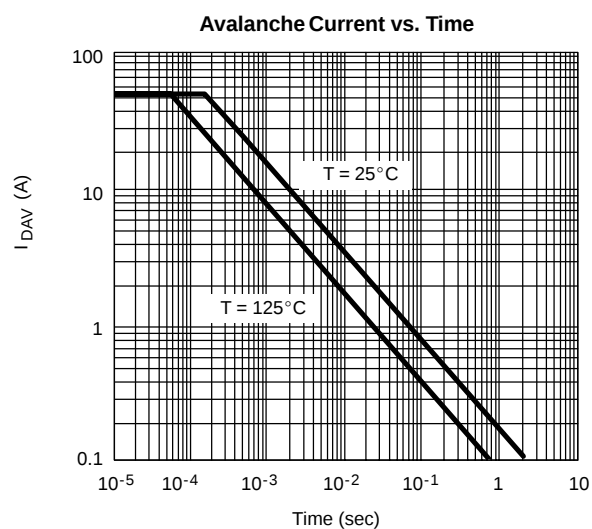
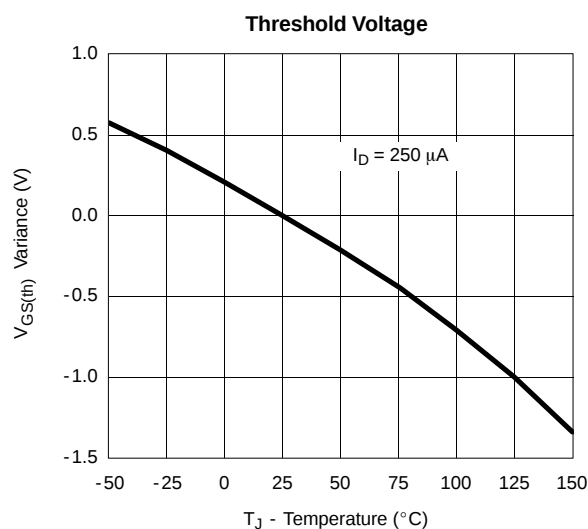
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

